NSN 5961-01-302-7880

Unitized Semiconductor Devices - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-302-7880 **Inclosure Material:** Ceramic **Overall Length:** 0.358 inches **Overall Height:** 0.100 inches **Overall Width:** 0.358 inches **Component Name And Quantity:** 2 semiconductor device diode and 2 transistor **Mounting Method:** Press fit **Semiconductor Material:** Silicon all transistor Voltage Rating In Volts Per Characteristic: 15.0 drain to source voltage all transistor **Current Rating Per Characteristic:** 100.00 microamperes forward current, dc all semiconductor device diode **Maximum Operating Tempurature Per Measurement Point:** 200.0 degrees celsius junction **Special Features:** All semiconductor device diode junction pattern arrangement: pn **Terminal Type And Quantity:** 20 uninsulated wire lead Shelf Life: N/a **Unit Of Measure:** Demilitarization: No

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